



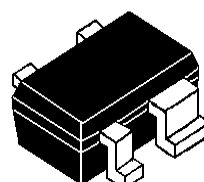
START499

NPN Silicon RF Transistor

- HIGH EFFICIENCY
- HIGH GAIN
- LINEAR AND NON LINEAR OPERATION
- TRANSITION FREQUENCY 42GHz
- ULTRA MINIATURE SOT343 (SC70) PACKAGE

DESCRIPTION

START499 is a product of the START family that provide the market with a Si state-of-art RF process. Manufactured in St 3rd generation bipolar process, it offers the highest power, gain and efficiency in SOT343 for given breakdown voltage (BV_{ceo}). Suitable for a wide range of applications up to 5GHz, it shows a performance level achieved before with GaAs products only.



SOT343 (SC70)

ORDER CODE
START499TR

BRANDING
499

APPLICATIONS

- PA FOR DECT OR PHS
- PA STAGE FOR WIRELESS LAN AND BLUETOOTH @ 2.5GHz
- UHF-VHF PRE POWER AMPLIFIER

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{ceo}	Collector emitter voltage	4.5	V
V _{cbo}	Collector base voltage	15	V
V _{ebo}	Emitter base voltage	1.5	V
I _c	Collector current	600	mA
I _b	Base current	32	mA
P _{tot}	Total dissipation at T _S = 60 °C	600	mW
T _{stg}	Storage temperature	-65 to 150	°C
T _j	Max. operating junction temperature	150	°C

ABSOLUTE MAXIMUM RATINGS

R _{thjs}	Thermal Resistance Junction soldering point	150	°C/W
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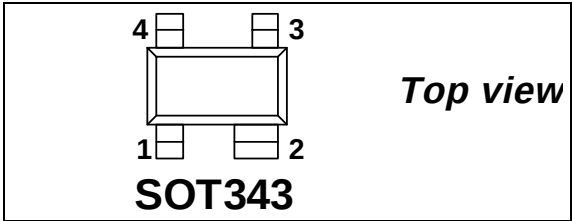
ELECTRICAL CHARACTERISTICS (T_j=25 °C,unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{cbo}	Collector cutoff current	V _{cb} = 5V, I _e = 0A			1.2	μA
I _{ebo}	Emitter-base cutoff current	V _{eb} = 1.5V, I _c = 0A			120	μA
H _{fe}	DC current gain	I _c = 160mA, V _{ce} = 4V		160		
G	Power gain	I _c =200mA, V _{ce} = 3V, f = 1.8GHz		15		dB
P _{-1dB}	1dB compression point	I _c = 200mA,V _{ce} = 3V, f = 1.8GHz		23.5		dBm
IP3	Ouput third order intercept point	I _c = 200mA,V _{ce} = 3V, f = 1.8GHz		33.5		dBm
NF	Noise Figure	I _c = 200mA,V _{ce} = 3V, f = 1.8GHz		3.3		dB

QUICK REFERENCE DATA

MODE OF OPERATION	f (GHz)	V _{CE} (V)	P _L (dBm)	G _p (dB)	η (%)
Class-AB (I _{cq} = 5mA)	1.9	3.6	26	≥12	typ. 68

PINOUT



PIN CONNECTION

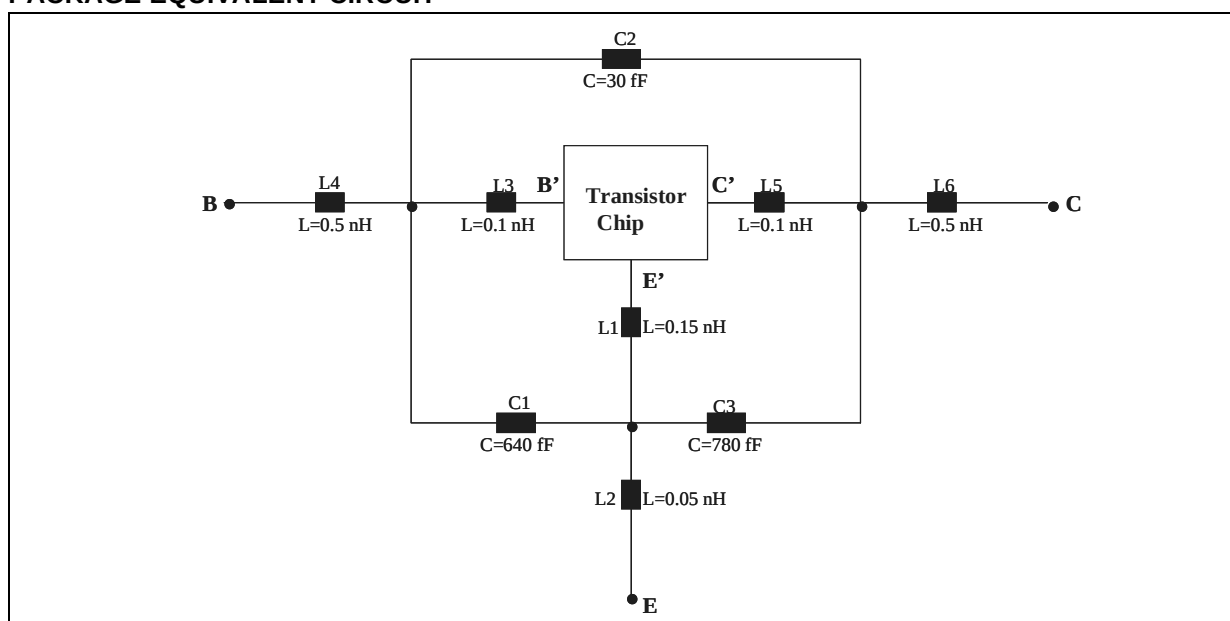
Pin No.	Description
1	BASE
3	COLLECTOR
2,4	EMITTER

SPICE PARAMETERS (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax)

TRANSISTOR CHIP DATA

Symbol	Value	Symbol	Value	Symbol	Value
TMEAS	27.0	FC	0.81	XJBC	0.51
IS	3.27E-16	EG	1.12	XTI	3.68
ISE	13.08E-12	NF	1	BF	332
NR	1	NE	3.2	VAF	70
ISC	7.89E-15	BR	9.75	VAR	2.1
IKF	$\{3.948*((T(^{\circ}C)+273.15)/300.15)^{-1.7}\}$	NC	1.5	TF	3.4E-12
TR	7E-10	PTF	38	VTF	29.7
XTF	16.3	ITF	5.01	MJE	0.341
RB	2.58	RBM	0.83	MJC	0.312
RC	0.597	RE	0.066	MJS	0.297
CJE	3048E-15	VJE	1.09	IKR	57.3E-3
CJC	930E-15	VJC	0.695	XTB	-0.82
CJS	510E-15	VJS	0.507		

PACKAGE EQUIVALENT CIRCUIT



In order to avoid high complexity of the package equivalent circuit, the two emitter leads of SOT-343 package are combined in one electrical connection.

FOR MORE ACCURACY SIMULATION IN SATURATION REGION :

Adding the 5 Spice parameters showed in Table A and using **ST Spice Library** (available on request) you can achieve a more accuracy simulation in the saturation region. ST Spice library is compatible with following simulators: ELDO MENTOR (any version), SPECTRE CADENCE (any version), ADS (version 2001 only).

Table A (Spice Parameters extracted in saturation region)

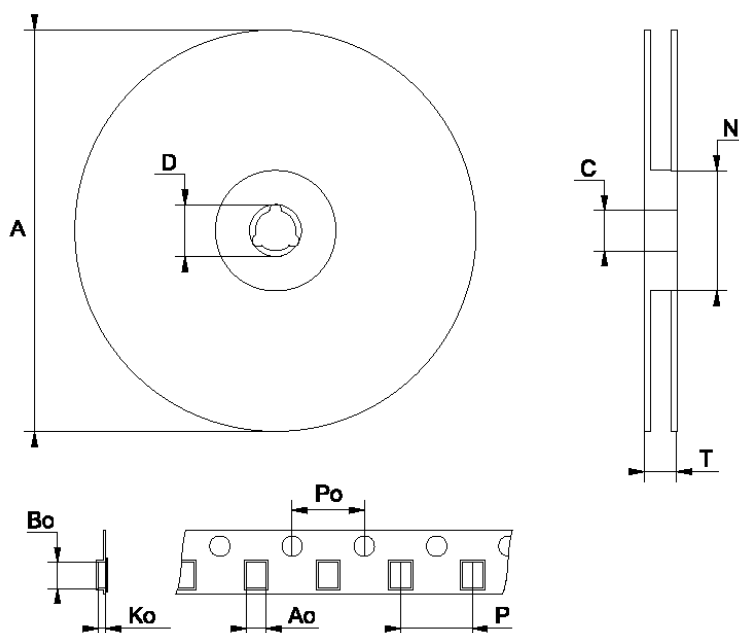
RW	Vjj	ENP	VRP	RP
1.034	0.755	2.235	$\{7.2*((TEMPER+273.15)/300.15)^{(0.125)}\}$	0.33E-6

START499**COMMON EMITTER S-PARAMETERS ($V_{CE} = 2V$, $I_C = 200mA$)**

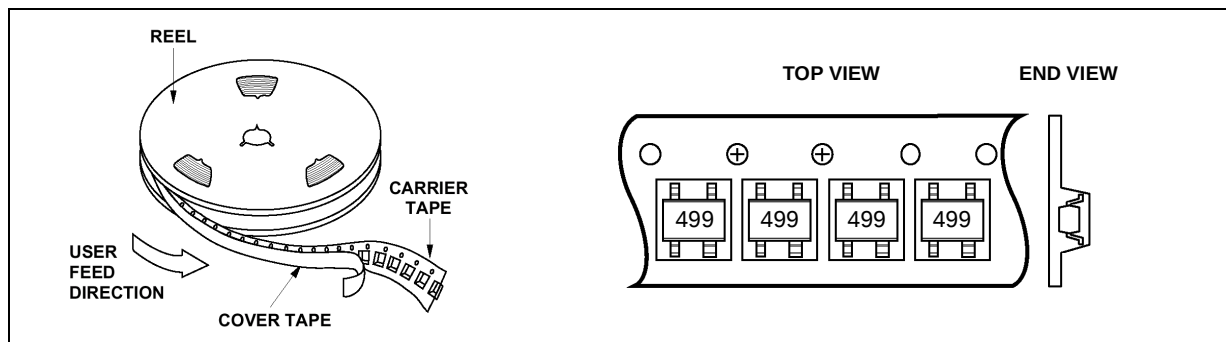
FREQ (MHz)	$ S_{11} $	$S_{11}\angle\Phi$	$ S_{21} $	$S_{21}\angle\Phi$	$ S_{12} $	$S_{12}\angle\Phi$	$ S_{22} $	$S_{22}\angle\Phi$
0.1	0.669	-158	65.164	124	0.008	47	0.635	-107
0.5	0.778	-179	15.773	105	0.013	81	0.589	-164
0.9	0.781	174	8.622	107	0.021	119	0.600	-174
1	0.780	173	7.535	109	0.021	134	0.598	-176
1.5	0.782	167	5.203	120	0.061	160	0.600	180
1.8	0.764	162	4.229	122	0.062	171	0.605	177
2	0.765	159	3.896	125	0.090	173	0.600	176
2.5	0.725	153	3.150	131	0.132	179	0.590	174
3	0.687	148	2.364	138	0.152	170	0.575	171
3.5	0.662	142	1.806	152	0.211	161	0.569	167
4	0.677	139	1.558	165	0.263	154	0.586	162

TAPE & REEL DIMENSIONS

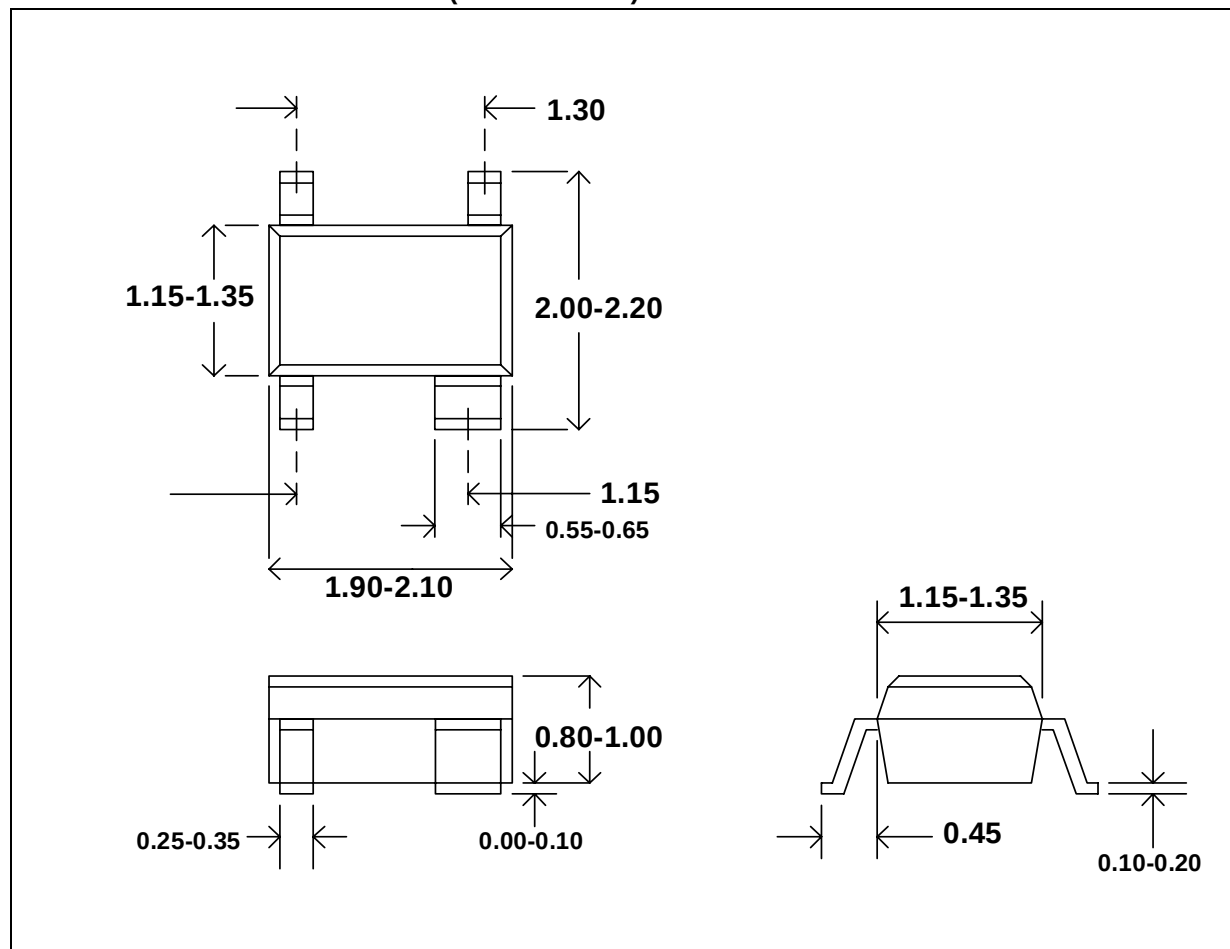
	mm		
	MIN.	TYP.	MAX
A	178.5	179	179.5
C	12.8	13.0	13.5
D	20.2		
N	54.5	55	55.5
T			14.4
Ao		2.25	
Bo		2.7	
Ko		1.2	
Po	3.8 (cumulative 10 Po)	4.0	4.2 (cumulative 10 Po)
P		4.0	



DEVICE ORIENTATION



PACKAGE DIMENSIONS SOT343 (SC-70 4 leads)



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